

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1430

Strobe Flash Applications
 Medium Power Amplifier Applications

- High DC current gain and excellent hFE linearity
 : hFE (1) = 140 to 600 (VCE = -1 V, IC = -0.5 A)
 : hFE (2) = 60 (min), 120 (typ.) (VCE = -1 V, IC = -4 A)
- Low saturation voltage: VCE (sat) = -0.5 V (max)
 (IC = -2 A, IB = -50 mA)

Absolute Maximum Ratings (Ta = 25°C)

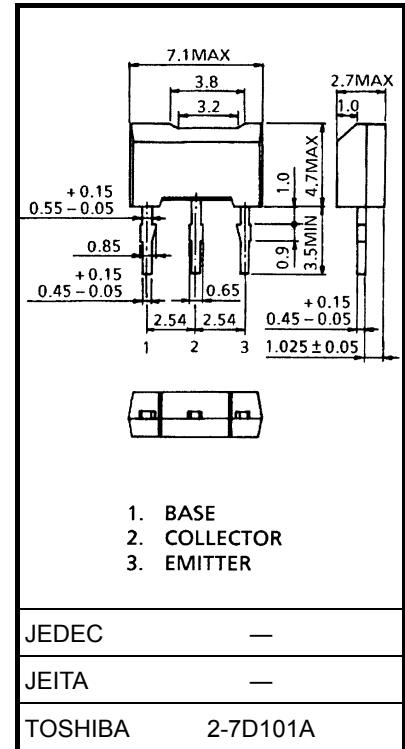
| Characteristics | | Symbol | Rating | Unit |
|-----------------------------|--------------------|------------------|------------|------|
| Collector-base voltage | | V _{CBO} | -20 | V |
| Collector-emitter voltage | | V _{CES} | -20 | V |
| | | V _{CEO} | -10 | |
| Emitter-base voltage | | V _{EBO} | -6 | V |
| Collector current | DC | I _C | -2 | A |
| | Pulsed (Note 1) | I _{CP} | -4 | |
| Base current | | I _B | -2 | A |
| Collector power dissipation | | P _C | 1000 | mW |
| Junction temperature | | T _j | 150 | °C |
| Storage temperature range | | T _{stg} | -55 to 150 | °C |

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



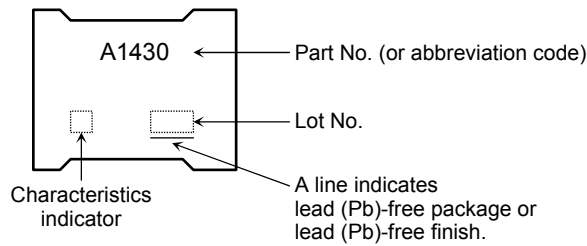
Weight: 0.2 g (typ.)

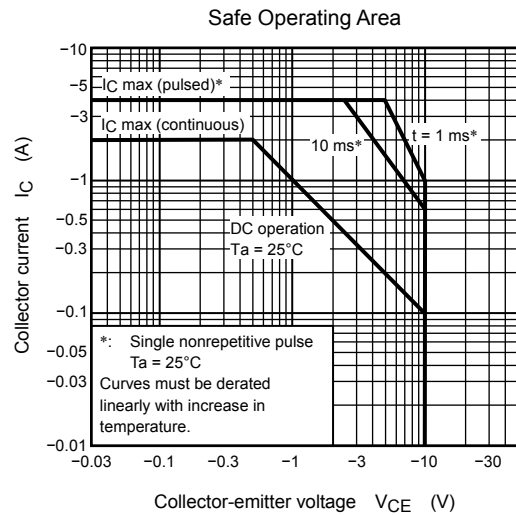
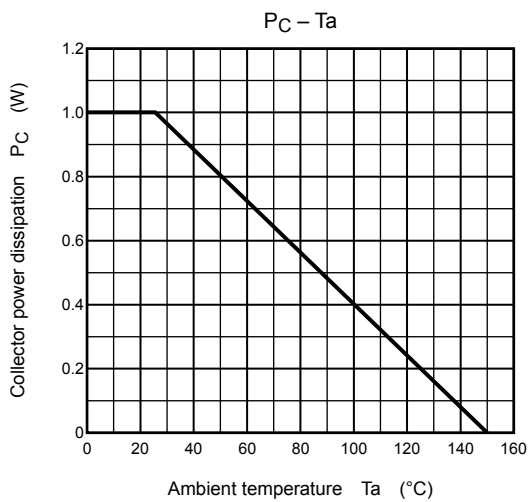
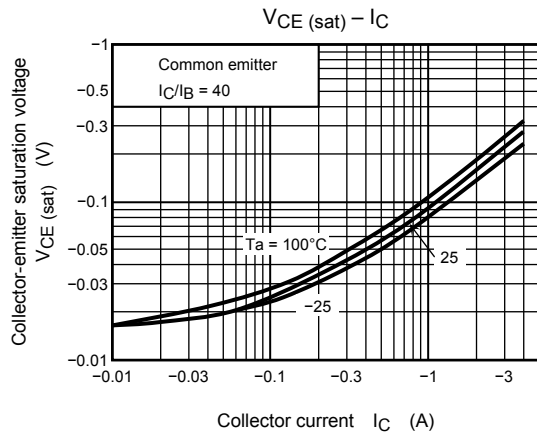
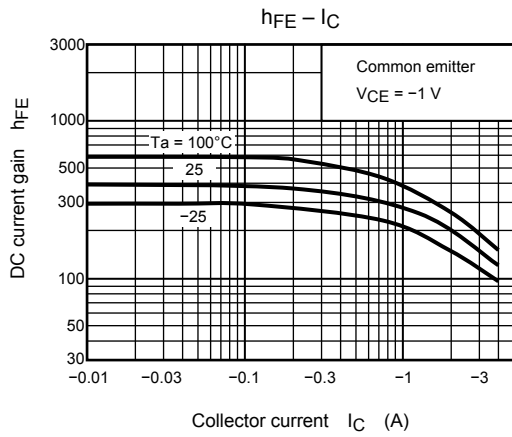
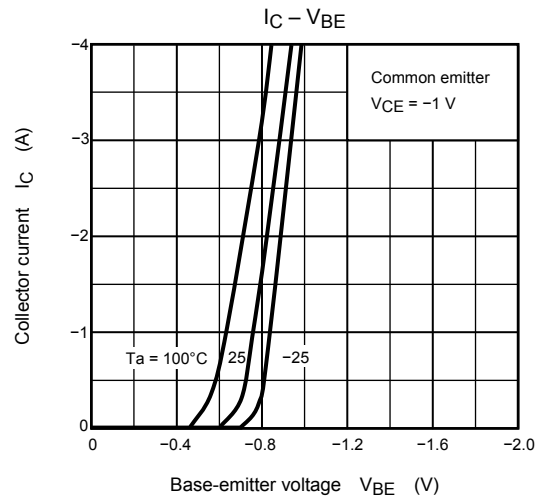
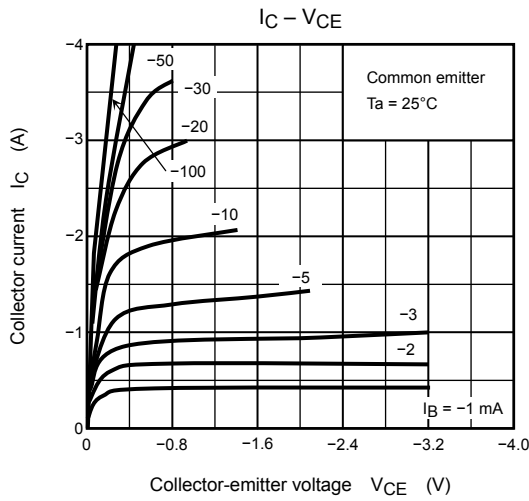
Electrical Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------------|--------------------------|----------------------------------------------------|-----|-------|-------|------|
| Collector cut-off current | I_{CBO} | $V_{CB} = -20\text{ V}, I_E = 0$ | — | — | -100 | nA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -6\text{ V}, I_C = 0$ | — | — | -100 | nA |
| Collector-emitter breakdown voltage | $V_{(BR) CEO}$ | $I_C = -10\text{ mA}, I_B = 0$ | -10 | — | — | V |
| Emitter-base breakdown voltage | $V_{(BR) EBO}$ | $I_E = -1\text{ mA}, I_C = 0$ | -6 | — | — | V |
| DC current gain | $h_{FE} (1)$ (Note 3) | $V_{CE} = -1\text{ V}, I_C = -0.5\text{ A}$ | 140 | — | 600 | |
| | $h_{FE} (2)$ | $V_{CE} = -1\text{ V}, I_C = -4\text{ A}$ | 60 | 120 | — | |
| Collector-emitter saturation voltage | $V_{CE (sat)}$ | $I_C = -2\text{ A}, I_B = -50\text{ mA}$ | — | -0.20 | -0.50 | V |
| Base-emitter voltage | V_{BE} | $V_{CE} = -1\text{ V}, I_C = -2\text{ A}$ | — | -0.83 | -1.5 | V |
| Transition frequency | f_T | $V_{CE} = -1\text{ V}, I_C = -0.5\text{ A}$ | — | 140 | — | MHz |
| Collector output capacitance | C_{ob} | $V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$ | — | 50 | — | pF |

Note 3: $h_{FE} (1)$ classification A: 140 to 280, B: 200 to 400, C: 300 to 600

Marking





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20070701-EN

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